

DATA SHEET

BTA225 series B Three quadrant triacs high commutation

Product specification

September 1997

Three quadrant triacs high commutation

BTA225 series B

GENERAL DESCRIPTION

Glass passivated high commutation triacs in a plastic envelope intended for use in circuits where high static and dynamic dV/dt and high dI/dt can occur loads. These devices will commutate the full rated rms current at the maximum rated junction temperature, without the aid of a snubber.

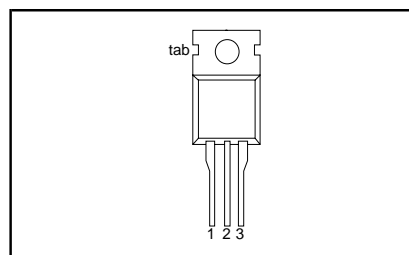
QUICK REFERENCE DATA

| SYMBOL | PARAMETER | MAX. | MAX. | MAX. | UNIT |
|--------------|--------------------------------------|--------------------|--------------------|--------------------|------|
| V_{DRM} | Repetitive peak off-state voltages | 500B 500 | 600B 600 | 800B 800 | V |
| $I_{T(RMS)}$ | RMS on-state current | 25 | 25 | 25 | A |
| I_{TSM} | Non-repetitive peak on-state current | 190 | 190 | 190 | A |

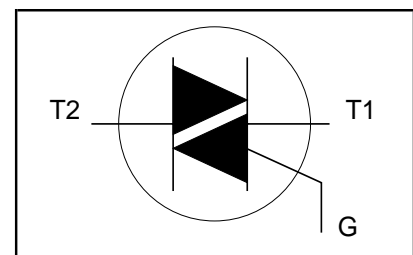
PINNING - TO220AB

| PIN | DESCRIPTION |
|-----|-----------------|
| 1 | main terminal 1 |
| 2 | main terminal 2 |
| 3 | gate |
| tab | main terminal 2 |

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | | | UNIT |
|--------------|--|--|------|------------------|------------------|------|------------------|
| | | | | -500 | -600 | -800 | |
| V_{DRM} | Repetitive peak off-state voltages | | - | 600 ¹ | 600 ¹ | 800 | V |
| $I_{T(RMS)}$ | RMS on-state current | full sine wave; $T_{mb} \leq 91\text{ °C}$ | - | 25 | | | A |
| I_{TSM} | Non-repetitive peak on-state current | full sine wave; $T_j = 25\text{ °C}$ prior to surge $t = 20\text{ ms}$ | - | 190 | | | A |
| I^2t | I^2t for fusing | $t = 16.7\text{ ms}$ | - | 209 | | | A |
| di_T/dt | Repetitive rate of rise of on-state current after triggering | $t = 10\text{ ms}$ $I_{TM} = 30\text{ A}; I_G = 0.2\text{ A}; di_G/dt = 0.2\text{ A}/\mu\text{s}$ | - | 180 | | | A ² s |
| I_{GM} | Peak gate current | | - | 2 | | | A |
| V_{GM} | Peak gate voltage | | - | 5 | | | V |
| P_{GM} | Peak gate power | | - | 5 | | | W |
| $P_{G(AV)}$ | Average gate power | over any 20 ms period | - | 0.5 | | | W |
| T_{stg} | Storage temperature | | -40 | 150 | | | °C |
| T_j | Operating junction temperature | | - | 125 | | | °C |

¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/μs.

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THERMAL RESISTANCES

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|--------------|---|-------------|------|------|------|------|
| R_{thj-mb} | Thermal resistance junction to mounting base | full cycle | - | - | 1.0 | K/W |
| | | half cycle | - | - | 1.4 | K/W |
| R_{thj-a} | Thermal resistance junction to ambient | in free air | - | 60 | - | K/W |

STATIC CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise stated

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|----------|-----------------------------------|---|------|------|------|------|
| I_{GT} | Gate trigger current ² | $V_D = 12\text{ V}; I_T = 0.1\text{ A}$ | | | | |
| | | T2+ G+ | 2 | 18 | 50 | mA |
| | | T2+ G- | 2 | 21 | 50 | mA |
| | | T2- G- | 2 | 34 | 50 | mA |
| I_L | Latching current | $V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$ | | | | |
| | | T2+ G+ | - | 31 | 60 | mA |
| | | T2+ G- | - | 34 | 90 | mA |
| | | T2- G- | - | 30 | 60 | mA |
| I_H | Holding current | $V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$ | - | 31 | 60 | mA |
| V_T | On-state voltage | $I_T = 30\text{ A}$ | - | 1.3 | 1.55 | V |
| V_{GT} | Gate trigger voltage | $V_D = 12\text{ V}; I_T = 0.1\text{ A}$ | - | 0.7 | 1.5 | V |
| | | $V_D = 400\text{ V}; I_T = 0.1\text{ A}; T_j = 125\text{ °C}$ | 0.25 | 0.4 | - | V |
| I_D | Off-state leakage current | $V_D = V_{DRM(max)}; T_j = 125\text{ °C}$ | - | 0.1 | 0.5 | mA |

DYNAMIC CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise stated

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|---------------|---|---|------|------|------|------------|
| dV_D/dt | Critical rate of rise of off-state voltage | $V_{DM} = 67\% V_{DRM(max)}; T_j = 125\text{ °C};$ exponential waveform; gate open circuit | 1000 | 4000 | - | V/ μ s |
| di_{com}/dt | Critical rate of change of commutating current | $V_{DM} = 400\text{ V}; T_j = 125\text{ °C}; I_{T(RMS)} = 25\text{ A};$ without snubber; gate open circuit | - | 44 | - | A/ms |
| t_{gt} | Gate controlled turn-on time | $I_{TM} = 30\text{ A}; V_D = V_{DRM(max)}; I_G = 0.1\text{ A};$ $di_G/dt = 5\text{ A}/\mu\text{s}$ | - | 2 | - | μ s |

² Device does not trigger in the T2-, G+ quadrant.

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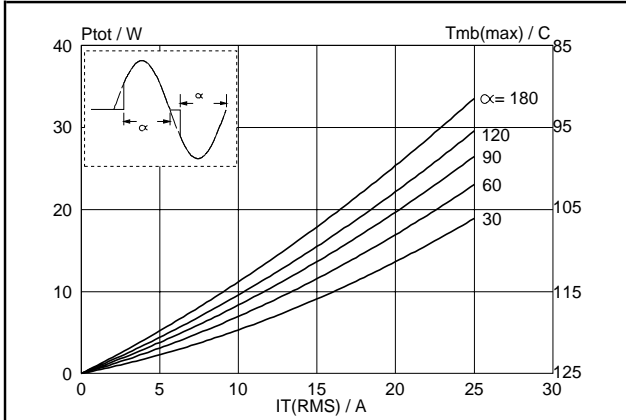


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where α = conduction angle.

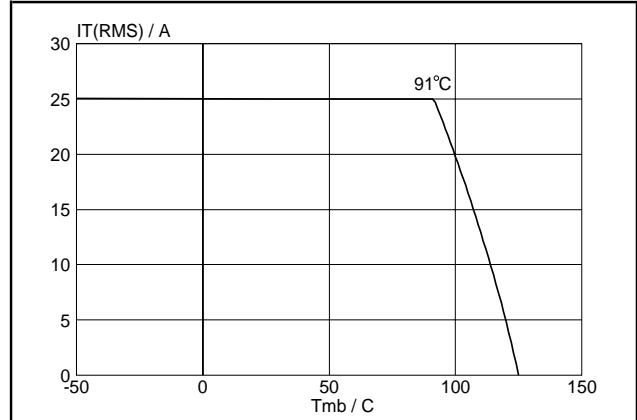


Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus mounting base temperature T_{mb} .

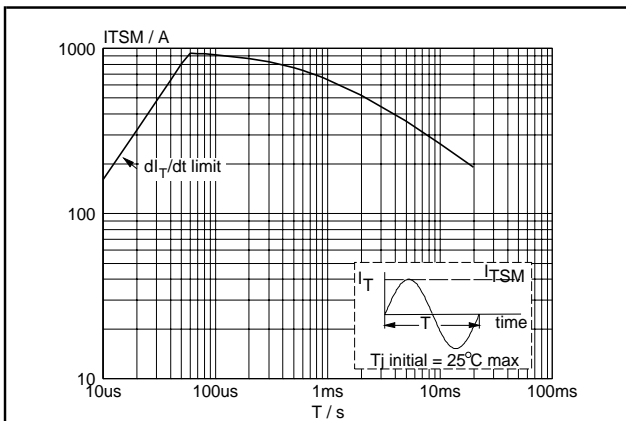


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \leq 20ms$.

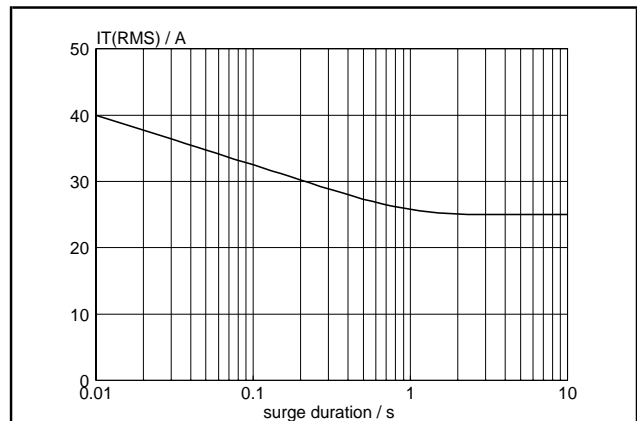


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, $f = 50$ Hz; $T_{mb} \leq 91$ °C.

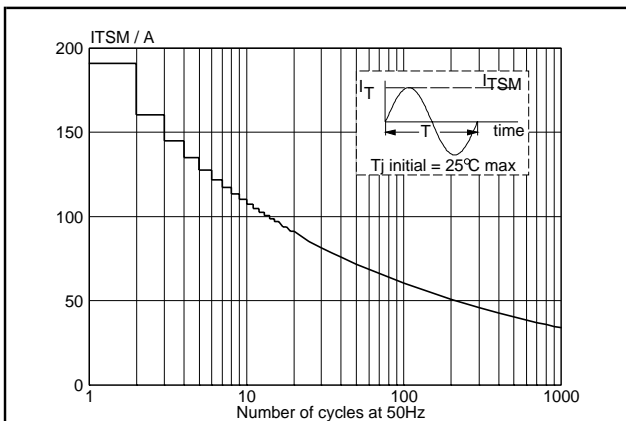


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, $f = 50$ Hz.

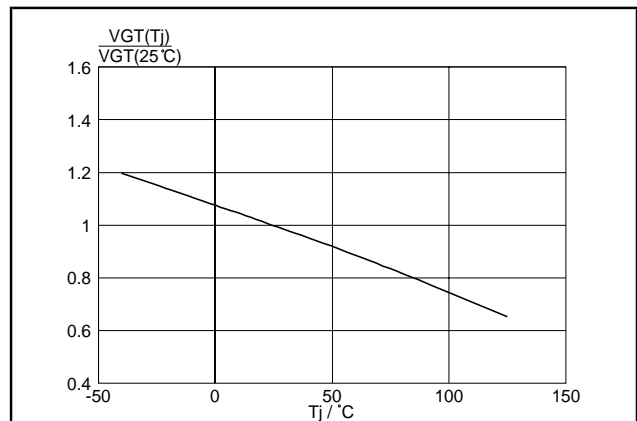
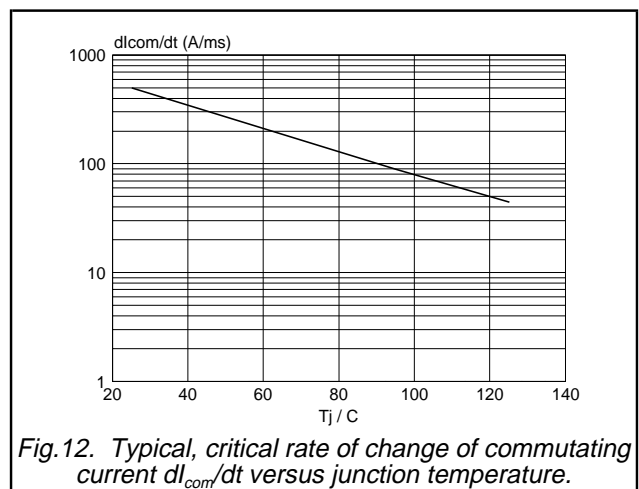
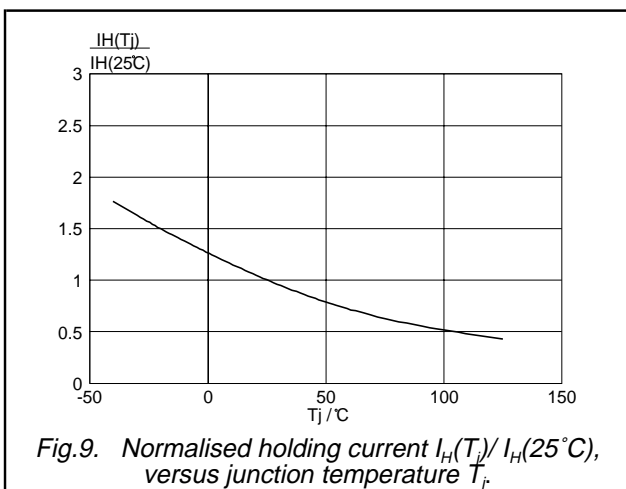
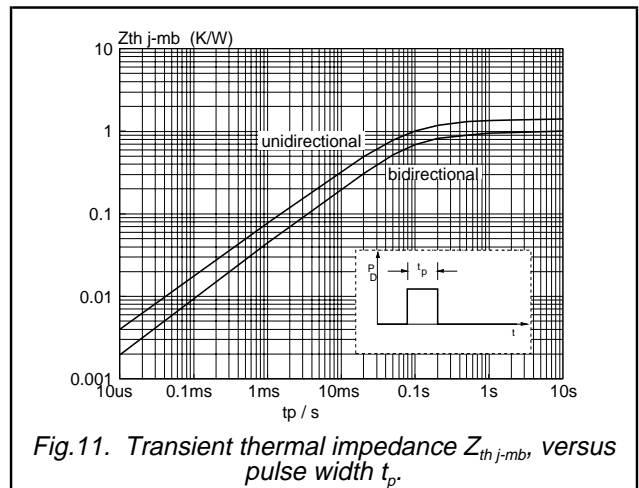
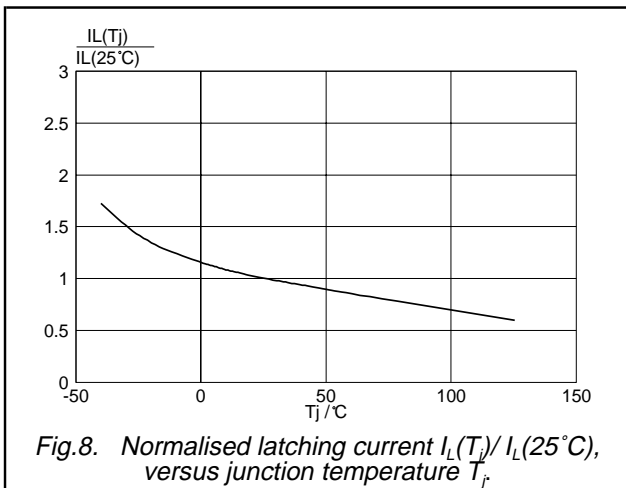
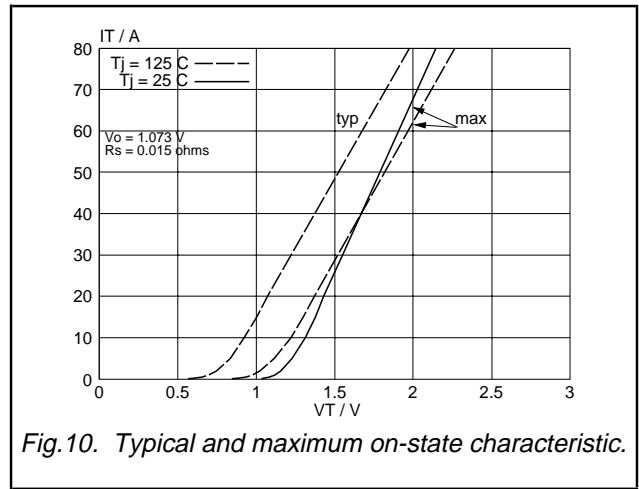
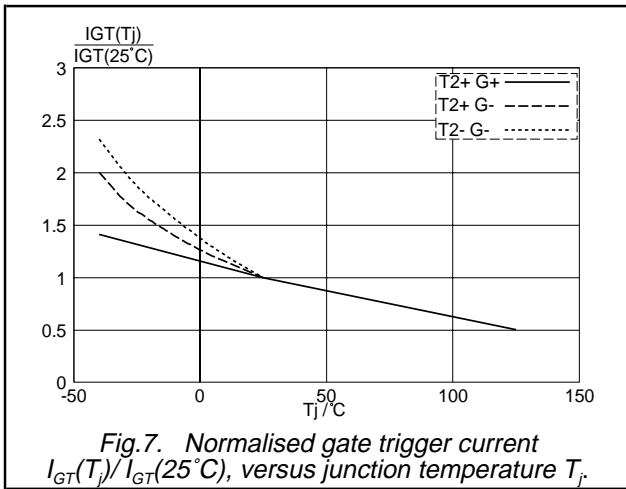


Fig.6. Normalised gate trigger voltage $V_{GT}(T_j) / V_{GT}(25^\circ C)$, versus junction temperature T_j .

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MECHANICAL DATA

Dimensions in mm

Net Mass: 2 g

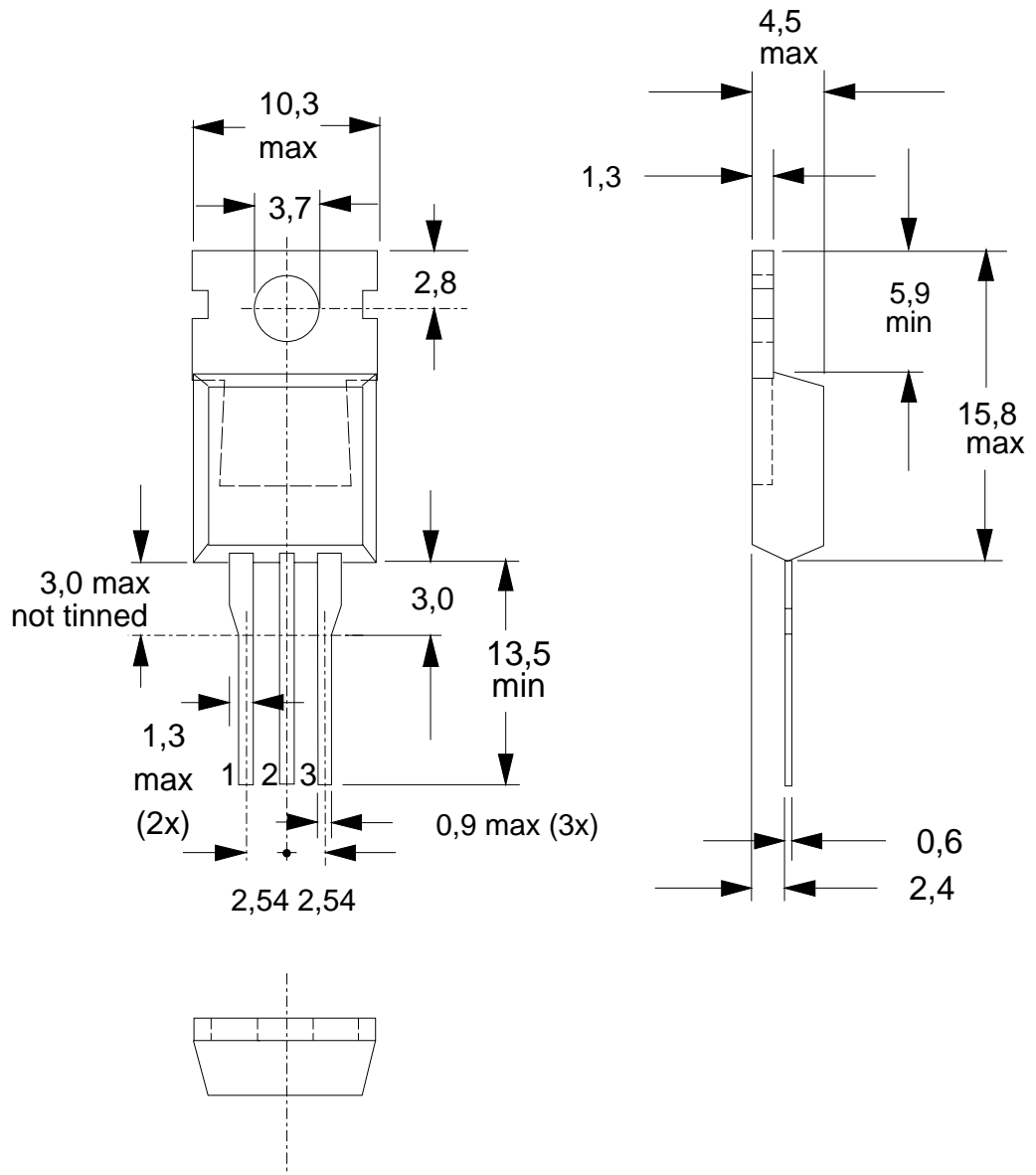


Fig.13. TO220AB; pin 2 connected to mounting base.

Notes

1. Refer to mounting instructions for TO220 envelopes.
2. Epoxy meets UL94 V0 at 1/8".

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DEFINITIONS

| Data sheet status | |
|--|---|
| Objective specification | This data sheet contains target or goal specifications for product development. |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |
| Limiting values | |
| Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability. | |
| Application information | |
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